Vishay Siliconix

HALOGEN

16 Ω , Low Charge Injection and Leakage, +12 V / +5 V / +3 V / ± 5 V Quad SPST Switches

DESCRIPTION

The DG441LE, DG442LE monolithic quad single-pole-single-throw analog switches are designed to provide high speed, low error switching of analog signals. The DG441LE has a normally closed function. The DG442LE has a normally open function.

The DG441LE, DG442LE feature low charge injection of a few picocoulombs over the full analog switch range. Combining low on resistance (16 Ω , typ.), low parasitic capacitance (C_{D(ON)} 15 pF), and fast switching speed (t_{ON}, 18 ns, typ.), the devices are ideal for data acquisition, sample-and-hold, and ADC input circuit designs.

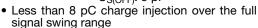
The DG441LE, DG442LE operate on single and dual supplies. Single supply voltage ranges from 3 V to 16 V while dual supply operation is recommended with \pm 3 V to \pm 8 V. Each switch conducts equally well in both direction when on, and blocks input voltages up to the supply levels when off.

The DG441LE, DG442LE are available in 16 lead TSSOP, SOIC, and PDIP packages.

FEATURES

- 3 V to 16 V single supply or ± 3 V to ± 8 V dual supply
- On-resistance R_{DS(on)}: 16 Ω
- Fast switching t_{ON}: 18 ns,typ.
- Low parasitic capacitance:

C_{D(ON)}: 15 pF C_{S(OFF)}: 5 pF



- Low leakage: < 10 pA, typ.
- TTL, CMOS compatible
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.

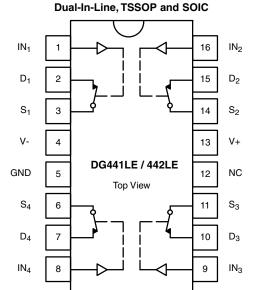
BENEFITS

- Wide operation voltage range
- · Low signal errors and distortion
- Fast switching time
- · Minimized switching glitch

APPLICATIONS

- Automatic test equipment
- Process control and automation
- Data acquisition systems
- Meters and instruments
- Medical and healthcare systems
- · Communication systems
- · Audio and video signal routing
- Relay replacement
- Battery powered systems

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE						
LOGIC	DG441LE	DG442LE				
0	On	Off				
1	Off	On				

Logic "0" \leq 0.8 V Logic "1" \geq 2.4 V

Document Number: 76754



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OODERING INFORMATION								
TEMP. RANGE	CONFIGURATION	PACKAGE	PART NUMBER	MIN. ORDER / PACK. QUANTITY				
		16-pin TSSOP	DG441LEDQ-GE3	Tube 360 units				
		10-ріі1 1330ғ	DG441LEDQ-T1-GE3	Tape and reel, 3000 units				
	DG441LE	16-pin SOIC	DG441LEDY-GE3	Tube 500 units				
			DG441LEDY-T1-GE3	Tape and reel, 2500 units				
-40 °C to +85 °C		16-pin PDIP	DG441LEDJ-GE3	Tube 500 units				
Lead (Pb)-free		10 T000D	DG442LEDQ-GE3	Tube 360 units				
		16-pin TSSOP	DG442LEDQ-T1-GE3	Tape and reel, 3000 units				
	DG442LE	16-pin SOIC	DG442LEDY-GE3	Tube 500 units				
		16-ріп 3010	DG442LEDY-T1-GE3	Tape and reel, 2500 units				
		16-pin PDIP	DG442LEDJ-GE3	Tube 500 units				

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)							
PARAMETER		SYMBOL	LIMIT	UNIT			
V+ to V-			-0.3 to +18				
GND to V-A			18	J			
Digital Inputs ^a V _S , V _D			GND -0.3 to (V +) + 0.3 or 30 mA, whichever occurs first				
Continuous Current (any terminal)			30	A			
Current, S or D (pulsed 1 ms, 10 % duty cycle)			100	mA			
Ctorogo Torogoroturo	(DQ, DY suffix)		-65 to +125	- °C			
Storage Temperature	(AK suffix)		-65 to +150				
	16-pin TSSOP °		450				
Power Dissipation (packages) b	16-pin narrow body SOIC ^d		650	mW			
	16-pin CerDIP ^e		900				
ESD Human Body Model (HBM); per ANSI / ESDA / JEDEC® JS-001			2500	V			
Latch Up Current, per JESD78D			400	mA			

Notes

- a. Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 7 mW/°C above 75 °C.
- d. Derate 7.6 mW/°C above 75 °C.
- e. Derate 12 mW/°C above 75 °C.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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SPECIFICATIONS ^a (single supply 12 V) TEST CONDITIONS A SUFFIX D SUFFIX									
		UNLESS OTHERWISE			LIMITS		LIMITS		
PARAMETER	SYMBOL	SPECIFIED V+ = 12 V, V- = 0 V	TEMP.b	TYP.°	-55 °C to	+125 °C	-40 °C t	o +85 °C	UNIT
		$V_{1N} = 12 \text{ V}, V_{1} = 0 \text{ V}$ $V_{1N} = 2.4 \text{ V}, 0.8 \text{ V}^{\text{f}}$			MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch			I.				ı	l	
Analog Signal Range ^e	V _{ANALOG}		Full	-	0	12	0	12	V
Drain-Source	R _{DS(on)}	V+ = 10.8 V, V- = 0 V	Room	16	-	26	-	26	
On-Resistance	TIDS(on)	$I_S = 10 \text{ mA}, V_D = 2 \text{ V} / 9 \text{ V}$	Full	-	-	40	-	35	Ω
On-Resistance Match Between Channels ^e	$\Delta R_{DS(on)}$	$I_S = 10 \text{ mA}, V_D = 9 \text{ V}$	Room	0.1	-	0.5	-	0.5	
	la		Room	-	-1	1	-1	1	
Switch Off Lookage Current	I _{S(off)}	$V_D = 1 V / 11 V$,	Full		-15	15	-10	10	
Switch Off Leakage Current	la con	$V_{S} = 11 \text{ V} / 1 \text{ V}$	Room		-1	1	-1	1	nA
	I _{D(off)}		Full	-	-15	15	-10	10	IIA
Channel On Leakage Current	I _{D(on)}	V _S = V _D = 11 V / 1 V	Room	-	-1	1	-1	1	-
Charmer On Leakage Current			Full	-	-15	15	-10	10	
Digital Control									
Input Current, V _{IN} Low	I _{IL}	V _{IN} under test = 0.8 V	Full	0.01	-1.5	1.5	-1	1	μΑ
Input Current, V _{IN} High	I _{IH}	V _{IN} under test = 2.4 V	Full	-	-1.5	1.5	-1	1	μΑ
Dynamic Characteristics									
Turn-On Time	t _{ON}	$R_L = 300 \Omega$, $C_L = 35 pF$ $V_S = 5 V$, see figure 2	Room	18	ı	60	-	60	
Turn-On Time			Full	-	-	80	-	70	ns
Turn-Off Time	t		Room	18	-	35	-	35	113
Turn-On Time	t _{OFF}		Full	-	ı	50	-	45	
Charge Injection ^e	Q	$V_g = 0~V,~R_g = 0~\Omega,~C_L = 10~nF$	Room	6.6	-	-	-	-	рС
Off Isolation ^e	OIRR	$R_L = 50 \Omega, C_L = 5 pF,$	Room	68.4	-	-	-	-	dB
Channel-to-Channel Crosstalk e	X _{TALK}	f = 1 MHz	Room	114	ı	-	-	-	uБ
Source Off Capacitance e	C _{S(off)}		Room	5	1	-	-	-	
Drain Off Capacitance e	C _{D(off)}	f = 1 MHz	Room	6	-	-	-	-	рF
Channel On Capacitance e	C _{D(on)}		Room	15	ı	-	-	-	
Power Supplies									
Positive Supply Current	l+		Full	0.03	-	1.5	-	1	
Negative Supply Current	1-	V _{IN} = 0 V or 12 V	Room	-	-1	-	-1	-	пΔ
riogative Supply Sufferit	1 =	VIN - 0 V OI 12 V	Full	0.002	-7.5	-	-5	-	μA
Ground Current	I _{GND}		Full	0.002	-1.5	_	-1	-	



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SPECIFICATIONS a (dual supply ± 5 V)									
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.b	TYP. °	A SUFFIX LIMITS -55 °C to +125 °C		D SUFFIX LIMITS -40 °C to +85 °C		UNIT
		V+ = 5 V, V- = -5 V V _{IN} = 2.4 V, 0.8 V ^f			MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch									
Analog Signal Range ^e	V_{ANALOG}		Full	-	-5	5	-5	5	V
Drain-Source On-Resistance	R _{DS(on)}	V+ = 5 V, V- = -5 V $I_S = 10 \text{ mA}, V_D = \pm 3.5 V$	Room Full	18 -	-	30 42	-	30 37	Ω
On-Resistance Match Between Channels ^e	$\Delta R_{DS(on)}$	$I_S = 10 \text{ mA}, V_D = \pm 3.5 \text{ V}$	Room	0.1	-	0.5	-	0.5	52
	-		Room	-	-1	1	-1	1	
Switch Off	I _{S(off)}	V+ = 5.5, V- = -5.5 V	Full	-	-15	15	-10	10	
Leakage Current ^g	l	$V_D = \pm 4.5 \text{ V}, V_S = \pm 4.5 \text{ V}$	Room	-	-1	1	-1	1	nA
	I _{D(off)}		Full	-	-15	15	-10	10	IIA
Channel On	1	V+ = 5.5 V, V- = -5.5 V	Room	-	-1	1	-1	1	
Leakage Current ^g	I _{D(on)}	$V_S = V_D = \pm 4.5 \text{ V}$	Full	-	-15	15	-10	10	
Digital Control									
Input Current, V _{IN} Low ^e	I _I L	V _{IN} under test = 0.8 V	Full	0.05	-1.5	1.5	-1	1	μA
Input Current, V _{IN} High ^e	I _{IH}	V _{IN} under test = 2.4 V	Full	0.05	-1.5	1.5	-1	1	μ, ,
Dynamic Characteristics				•	r	,	•	•	
Turn-On Time	t _{ON}	ton		42	-	65	-	65	
	ON	$R_L = 300 \Omega$, $C_L = 35 pF$	Full	-	-	90	-	75	ns
Turn-Off Time	t _{OFF}	$V_S = \pm 3.5 \text{ V}$, see figure 2	Room	34	-	45	-	45	
			Full	-	-	65	-	55	
Charge Injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	5.8	-	-	-	-	рС
Off Isolation e	OIRR		Room	68.4	-	-	-	-	
Channel-to-Channel Crosstalk ^e	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	113	-	-	-	-	dB
Source Off Capacitance e	C _{S(off)}		Room	5	-	-	-	-	
Drain Off Capacitance e	C _{D(off)}	f = 1 MHz	Room	6	-	-	-	-	pF
Channel On Capacitance e	C _{D(on)}		Room	14	-	-	-	-	
Power Supplies									
Positive Supply Current ^e	I+		Full	0.002	-	1.5	-	1	
Negative Supply Current e	1-	V _{IN} = 0 V or 5 V	Room	-0.002	-1	-	-1	-	μA
regative capply carrent		1111 - 0 1 01 0 1	Full	_	-7.5	-	-5	-	



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SPECIFICATIONS ^a (single supply ± 5 V)									
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.b	P.b TYP.c	A SUFFIX LIMITS -55 °C to +125 °C		D SUFFIX LIMITS -40 °C to +85 °C		UNIT
		V+ = 5 V, V- = 0 V $V_{IN} = 2.4 V, 0.8 V f$			MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full	-	-	5	-	5	V
Drain-Source	D	V + = 4.5 V	Room	36	-	50	-	50	
On-Resistance e	R _{DS(on)}	$I_S = 5 \text{ mA}, V_D = 1 \text{ V}, 3.5 \text{ V}$	Full	-	-	88	-	75	Ω
On-Resistance Match Between Channels ^e	$\Delta R_{DS(on)}$	$I_S = 10 \text{ mA}, V_D = 3.5 \text{ V}$	Room	0.5	-	1	-	1	32
Dynamic Characteristics									
Turn-On Time e	+		Room	53	-	70	-	70	
rum-on nine	t _{ON}	$R_L = 300 \Omega, C_L = 35 pF$	Hot	-	-	90	-	80	ns
Turn-Off Time e	+	$V_S = 3.5 V$, see figure 2	Room	34	-	50	-	50	115
rum-on nine °	t _{OFF}		Hot	-	-	70	-	60	
Charge Injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	3.3	-	-	-	-	рC
Power Supplies									
Positive Supply Current ^e	I+		Full	10	-	200	-	100	
Negative Supply Current e	1-	V _{IN} = 0 V or 5 V	Room	-0.002	-1	-	-1	-	μA
Negative Supply Current	'-	VIN = 0 V OI 5 V	Full	-	-7.5	-	-5	-	μΑ
Ground Current ^e	I _{GND}		Full	-10	-200	-	-100	-	



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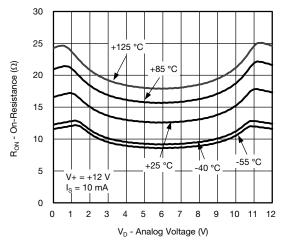
SPECIFICATIONS a (single supp	oly 3 V)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.b	b TYP. c	A SUFFIX LIMITS -55 °C to +125 °C		D SUFFIX LIMITS -40 °C to +85 °C		UNIT
		V+ = 3 V, V- = 0 V $V_{IN} = 0.4 V^f$			MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full	-	0	3	0	3	V
Drain-Source On-Resistance	R _{DS(on)}	V+ = 2.7 V, V- = 0 V $I_S = 5 mA, V_D = 0.5 V, 2.2 V$	Room Full	106	-	130 150	-	130 140	0
On-Resistance Match Between Channels ^e	$\Delta R_{DS(on)}$	$I_S = 5 \text{ mA}, V_D = 2.2 \text{ V}$	Room	1	-	3	-	3	Ω
			Room	-	-1	1	-1	1	
Switch Off	I _{S(off)}	V+ = 3.3, V- = 0 V	Full	-	-15	15	-10	10	
Leakage Current ^g	I _{D(off)}	$V_D = 1 \text{ V}, 2 \text{ V}, V_S = 2 \text{ V}, 1 \text{ V}$	Room	-	-1	1	-1	1	nA
			Full	-	-15	15	-10	10	
Channel On		V+ = 3.3 V, V- = 0 V	Room	-	-1	1	-1	1	
Leakage Current ^g	I _{D(on)}	$V_S = V_D = 1 V, 2 V$	Full	-	-15	15	-10	10	
Digital Control									
Input Current, V _{IN} Low ^e	I _{IL}	V _{IN} under test = 0.4 V	Full	0.005	-1.5	1.5	-1	1	μA
Input Current, V _{IN} High ^e	I _{IH}	V _{IN} under test = 2.4 V	Full	0.005	-1.5	1.5	-1	1	μΑ
Dynamic Characteristics									
Turn-On Time	+		Room	141	-	200	-	200	
Turri-Ori Time	t _{ON}	$R_L = 300 \Omega, C_L = 35 pF$	Full	-	-	220	-	210	ns
Turn-Off Time	+	$V_S = 1.5 V$, see figure 2	Room	84	-	120	-	120	115
Turri-Ori Tirrie	t _{OFF}		Full	-	-	140	-	130	
Charge Injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	2	-	-	-	-	рС
Off Isolation e	OIRR		Room	68	-	-	-	-	
Channel-to-Channel Crosstalk ^e	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	107	-	-	-	-	dB
Source Off Capacitance e	C _{S(off)}		Room	6	-	-	-	-	
Drain Off Capacitance e	C _{D(off)}	f = 1 MHz	Room	7	-	=	-	-	pF
Channel On Capacitance e	C _{D(on)}		Room	15	-	-	-	-	

Notes

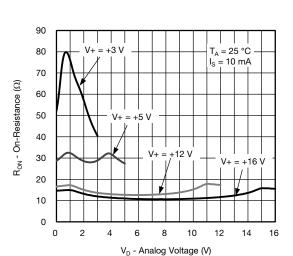
- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25 °C, full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.
- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test.



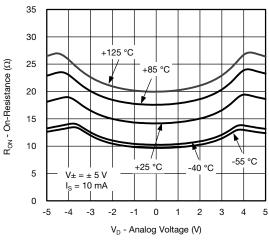
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



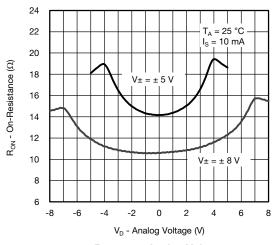
R_{DS(on)} vs. Analog Voltage and Temperature



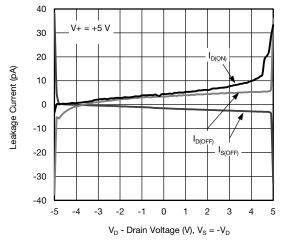
R_{DS(on)} vs. Analog Voltage



R_{DS(on)} vs. Drain Voltage and Temperature



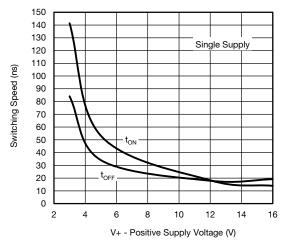
R_{DS(on)} vs. Analog Voltage



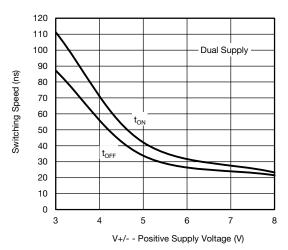
Leakage Current vs. Drain Voltage (Dual Supply)



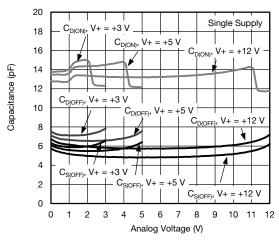
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



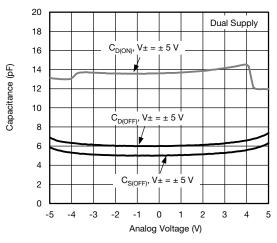
Switching Time vs. Single Supply



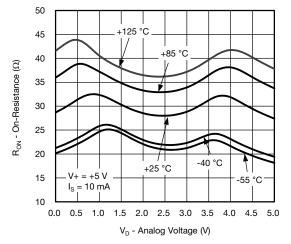
Switching Time vs. Dual Supply



Capacitance vs. Analog Voltage (Single Supply)



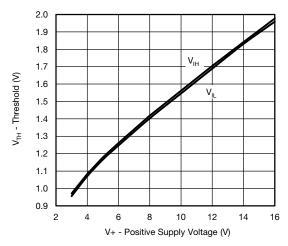
Capacitance vs. Analog Voltage (Dual Supply)



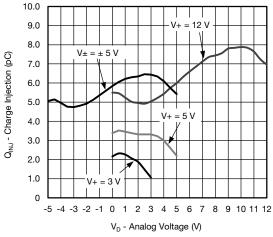
R_{DS(on)} vs. Analog Voltage and Temperature



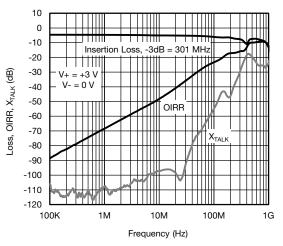
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



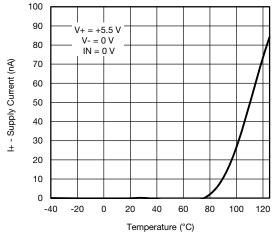
Input Threshold vs. Single Supply Voltage



Charge Injection vs. Analog Voltage



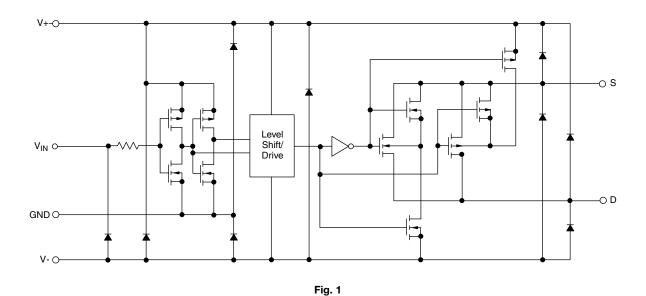
Insertion Loss, Off Isolation and Crosstalk vs. Frequency (Single Supply)



Supply Current vs. Temperature



SCHEMATIC DIAGRAM (typical channel)



TEST CIRCUITS

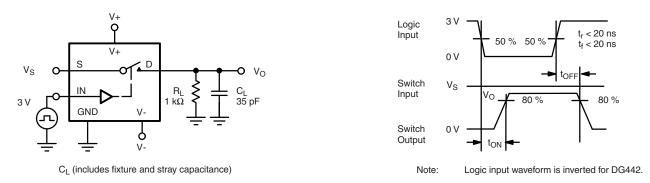


Fig. 2 - Switching Time

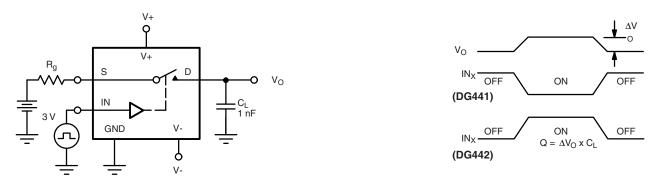


Fig. 3 - Charge Injection

TEST CIRCUITS

C = 1 μF tantalum in parallel with 0.01 μF ceramic 50Ω IN_1 NC o 0 V, 2.4 V O GND X_{TALK} Isolation = 20 log C = RF bypass

Fig. 4 - Crosstalk

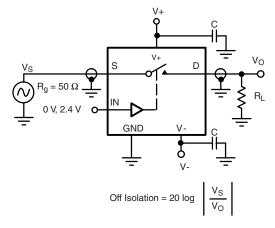


Fig. 5 - Off Isolation

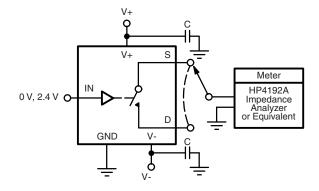


Fig. 6 - Source / Drain Capacitances



APPLICATIONS

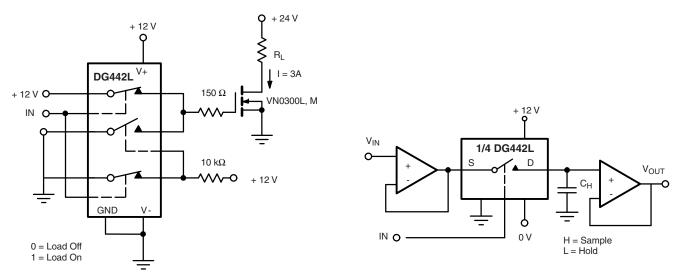


Fig. 7 - Power MOSFET Driver

Fig. 8 - Open Loop Sample-and-Hold

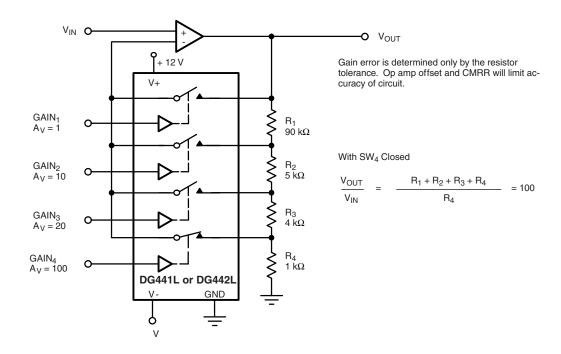


Fig. 9 - Precision-Weighted Resistor Programmable-Gain Amplifier

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?76754.



SOIC (NARROW): 16-LEAD JEDEC Part Number: MS-012



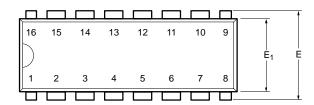
	MILLIMETERS		INC	HES			
Dim	Min	Max	Min	Max			
Α	1.35	1.75	0.053	0.069			
A ₁	0.10	0.20	0.004	0.008			
В	0.38	0.51	0.015	0.020			
С	0.18	0.23	0.007	0.009			
D	9.80	10.00	0.385	0.393			
Е	3.80	4.00	0.149	0.157			
е	1.27	1.27 BSC		BSC			
Н	5.80	6.20	0.228	0.244			
L	0.50	0.93	0.020	0.037			
0	0°	8°	0°	8°			
ECN: S-0	ECN: S-03946—Rev. F, 09-Jul-01						

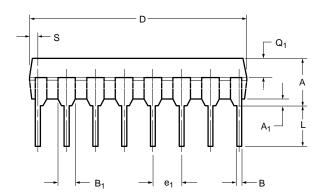
DWG: 5300

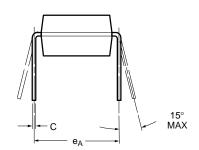




PDIP: 16-LEAD







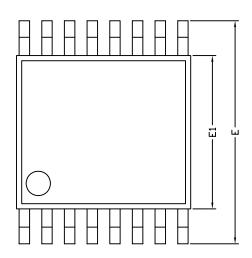
	MILLIN	IETERS	INC	HES		
Dim	Min	Max	Min	Max		
Α	3.81	5.08	0.150	0.200		
A ₁	0.38	1.27	0.015	0.050		
В	0.38	0.51	0.015	0.020		
B ₁	0.89	1.65	0.035	0.065		
С	0.20	0.30	0.008	0.012		
D	18.93	21.33	0.745	0.840		
E	7.62	8.26	0.300	0.325		
E ₁	5.59	7.11	0.220	0.280		
e ₁	2.29	2.79	0.090	0.110		
e _A	7.37	7.87	0.290	0.310		
L	2.79	3.81	0.110	0.150		
Q ₁	1.27	2.03	0.050	0.080		
S	0.38	1.52	.015	0.060		
ECN: S-03946—Rev. D, 09-Jul-01						

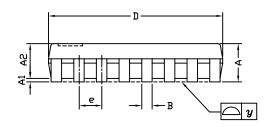
DWG: 5482

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TSSOP: 16-LEAD







	DIMENSIONS IN MILLIMETERS					
Symbols	Min	Nom	Max			
A	-	1.10	1.20			
A1	0.05	0.10	0.15			
A2	-	1.00	1.05			
В	0.22	0.28	0.38			
С	-	0.127	-			
D	4.90	5.00	5.10			
E	6.10	6.40	6.70			
E1	4.30	4.40	4.50			
е	-	0.65	-			
L	0.50	0.60	0.70			
L1	0.90	1.00	1.10			
у	-	-	0.10			
θ1	0°	3°	6°			
ECN: S-61920-Rev D 23	R-Oct-06					

ECN: S-61920-Rev. D, 23-Oct-06

DWG: 5624

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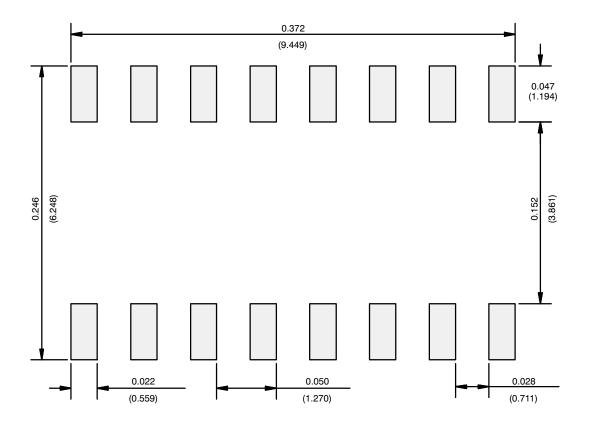
RECOMMENDED MINIMUM PAD FOR TSSOP-16



Recommended Minimum Pads Dimensions in inches (mm)



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

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